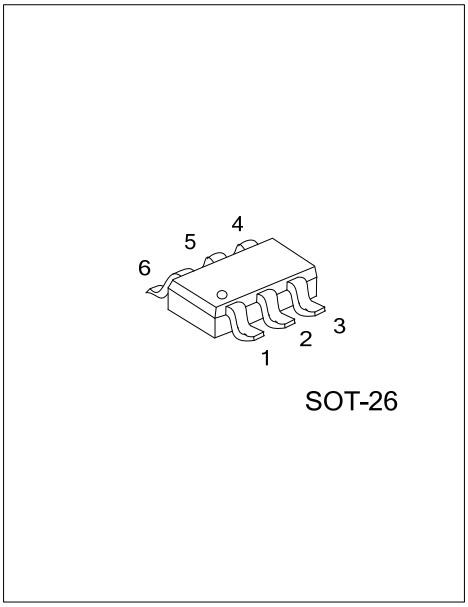
IMZ88

DUAL TRANSISTOR

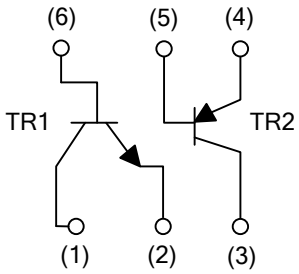
GENERAL PURPOSE (DUAL TRANSISTOR)



■ FEATURES

*Both a 8550S chip and 8050S chip in a SMT package

■ EQUIVALENT CIRCUITS



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment						Packing
		1	2	3	4	5	6	
IMZ88G-AG6-R	SOT-26	C1	E1	C2	E2	B2	B1	Tape Reel

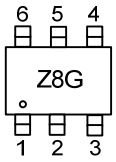
Note: Pin assignment: E: Emitter B: Base C: Collector

IMZ88G-AG6-R

(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel
(2) AG6: SOT-26
(3) G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A= 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNIT
Collector-Base Voltage	TR1	V_{CBO}	30	V
	TR2		-30	
Collector-Emitter Voltage	TR1	V_{CEO}	20	V
	TR2		-20	
Emitter-Base Voltage	TR1	V_{EBO}	5	V
	TR2		-5	
Collector Current	TR1	I_C	700	mA
	TR2		-700	
Power Dissipation (Note 2)		P_D	300	mW
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. 200mW per element must not be exceeded.

■ ELECTRICAL CHARACTERISTICS (T_A= 25°C, unless otherwise specified)

TR1

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA,I_E=0	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA,I_B=0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=100μA,I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V			1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V			100	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=500mA, I_B=50mA			0.5	V
Base-emitter saturation voltage	$V_{BE(SAT)}$	I_C=500mA, I_B=50mA			1.2	V
Base-emitter saturation voltage	V_{BE}	V_{CE}=1V, I_C=10mA			1.0	V
ON CHARACTERISTICS						
DC Current Transfer Ratio	h_{FE1}	V_{CE}=1V, I_C = 1mA	100			
	h_{FE2}	V_{CE}=1V, I_C=150mA	120		400	
	h_{FE3}	V_{CE}=1V, I_C=500mA	40			
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	V_{CE}=10V, I_C=50mA	100			MHz
Output Capacitance	C_{OB}	V_{CB}=10V, I_E=0, f=1MHz		9.0		pF

■ ELECTRICAL CHARACTERISTICS(Cont.)

TR2

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA,I_E=0	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -1mA, I_B=0	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA,I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V,I_E=0			-1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}= -5V, I_C=0			-100	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-500mA, I_B=-50mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(SAT)}$	I_C= 500mA, I_B=-50mA			-1.2	V
Base-emitter saturation voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA			-1.0	V
ON CHARACTERISTICS						
DC Current Transfer Ratio	h_{FE1}	V_{CE}= -1V, I_C = -1mA	100			
	h_{FE2}	V_{CE}=-1V, I_C=-150mA	120		400	
	h_{FE3}	V_{CE}=-1V, I_C=-500mA	40			
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	V_{CE}=-10V,I_C=-50mA	100			MHz
Output Capacitance	C_{OB}	V_{CB}=10V,I_E=0, f=1MHz		9.0		pF